

# NTB5860NL, NTP5860NL, NVB5860NL



ON Semiconductor®

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## N-Channel Power MOSFET

60 V, 220 A, 3.0 mΩ

### Features

- Low  $R_{DS(on)}$
- High Current Capability
- 100% Avalanche Tested
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant
- NVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ Unless otherwise specified)

Parameter	Symbol	Value	Unit		
Drain-to-Source Voltage	$V_{DSS}$	60	V		
Gate-to-Source Voltage – Continuous	$V_{GS}$	$\pm 20$	V		
Continuous Drain Current, $R_{\theta JC}$	$I_D$	$T_A = 25^\circ\text{C}$	220		
		$T_A = 100^\circ\text{C}$	156		
Power Dissipation, $R_{\theta JC}$	Steady State	$T_A = 25^\circ\text{C}$	$P_D$	283	W
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	$I_{DM}$	660	A	
Current Limited by Package	$I_{DMmax}$	130	A		
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$		
Source Current (Body Diode)	$I_S$	130	A		
Single Pulse Drain-to-Source Avalanche Energy ( $L = 0.3 \text{ mH}$ )	$E_{AS}$	735	mJ		
Lead Temperature for Soldering Purposes (1/8" from Case for 10 Seconds)	$T_L$	260	$^\circ\text{C}$		

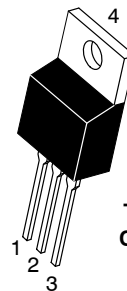
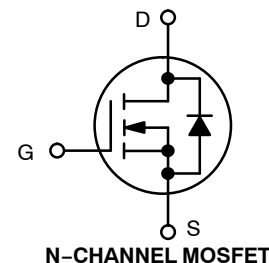
### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Case (Drain) Steady State	$R_{\theta JC}$	0.53	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	28	

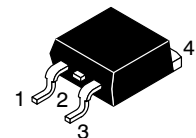
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1 sq in pad size, (Cu Area 1.127 sq in [2 oz] including traces).

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	$I_D$ MAX
60 V	3.0 mΩ @ 10 V	220 A
	3.6 mΩ @ 4.5 V	

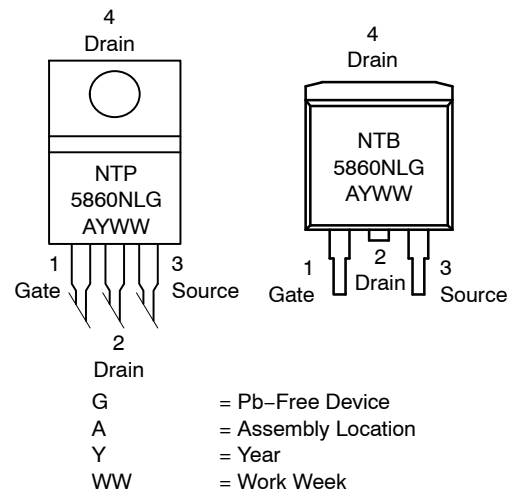


TO-220AB  
CASE 221A  
STYLE 5



D2PAK  
CASE 418B  
STYLE 2

### MARKING DIAGRAMS & PIN ASSIGNMENTS



### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

# NTB5860NL, NTP5860NL, NVB5860NL

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C Unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>DS</sub> = 0 V, I <sub>D</sub> = 250 μA	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA		6.1		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V V <sub>DS</sub> = 60 V	T <sub>J</sub> = 25°C		1.0	μA
		V <sub>GS</sub> = 0 V V <sub>DS</sub> = 60 V	T <sub>J</sub> = 125°C		100	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V			± 100	nA

### ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA	1.0		3.0	V
Threshold Temperature Coefficient	V <sub>GS(th)</sub> /T <sub>J</sub>			-7.7		mV/°C
Drain-to-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		2.4	3.0	mΩ
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A		2.8	3.6	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A		47		S

### CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz		13216		pF
Output Capacitance	C <sub>oss</sub>			1127		
Transfer Capacitance	C <sub>rss</sub>			752		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 48 V, I <sub>D</sub> = 40 A		220		nC
Threshold Gate Charge	Q <sub>G(TH)</sub>			13		
Gate-to-Source Charge	Q <sub>GS</sub>			37		
Gate-to-Drain Charge	Q <sub>GD</sub>			54		

### SWITCHING CHARACTERISTICS, V<sub>GS</sub> = 10 V (Note 3)

Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = 10 V, V <sub>DD</sub> = 48 V, I <sub>D</sub> = 100 A, R <sub>G</sub> = 2.5 Ω		25		ns
Rise Time	t <sub>r</sub>			58		
Turn-Off Delay Time	t <sub>d(off)</sub>			98		
Fall Time	t <sub>f</sub>			144		

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V I <sub>S</sub> = 40 A	T <sub>J</sub> = 25°C		0.76	1.1	V <sub>dc</sub>
			T <sub>J</sub> = 125°C		0.60		
Reverse Recovery Time	t <sub>rr</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 100 A, dI <sub>S</sub> /dt = 20 A/μs		50		ns	
Charge Time	t <sub>a</sub>			25			
Discharge Time	t <sub>b</sub>			25			
Reverse Recovery Stored Charge	Q <sub>RR</sub>			71			nC

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

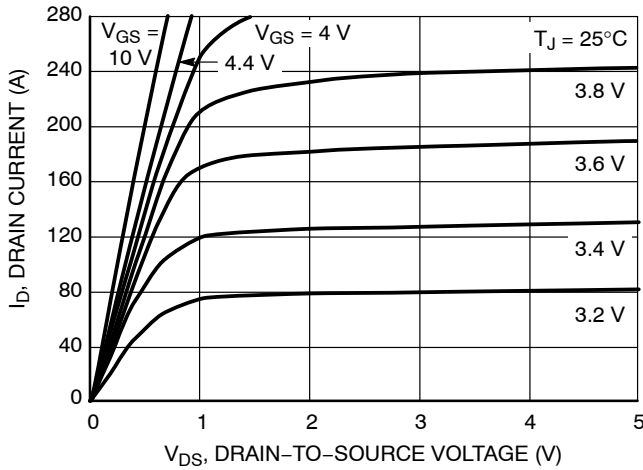


Figure 1. On-Region Characteristics

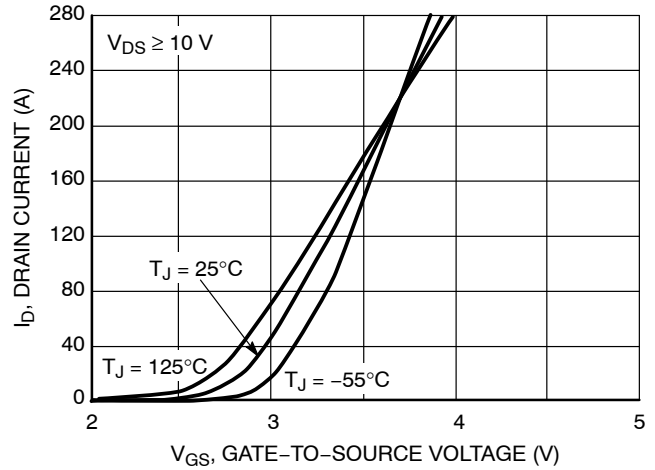


Figure 2. Transfer Characteristics

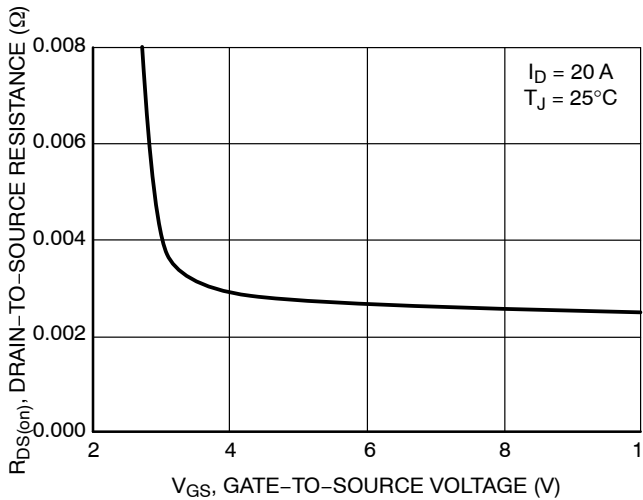


Figure 3. On-Resistance vs. Gate Voltage

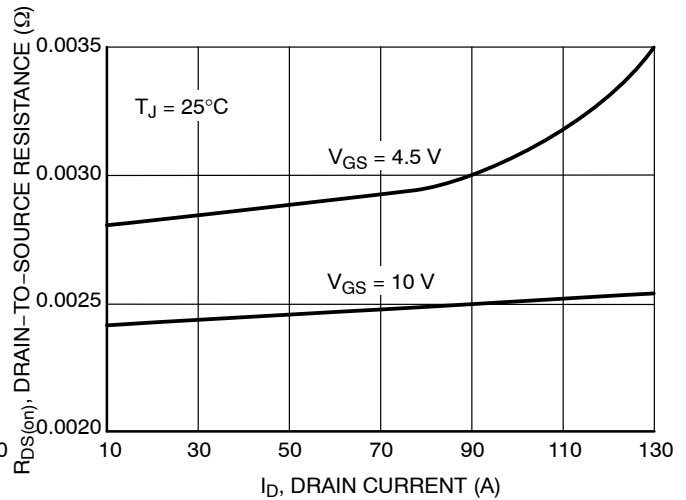


Figure 4. On-Resistance vs. Drain Current

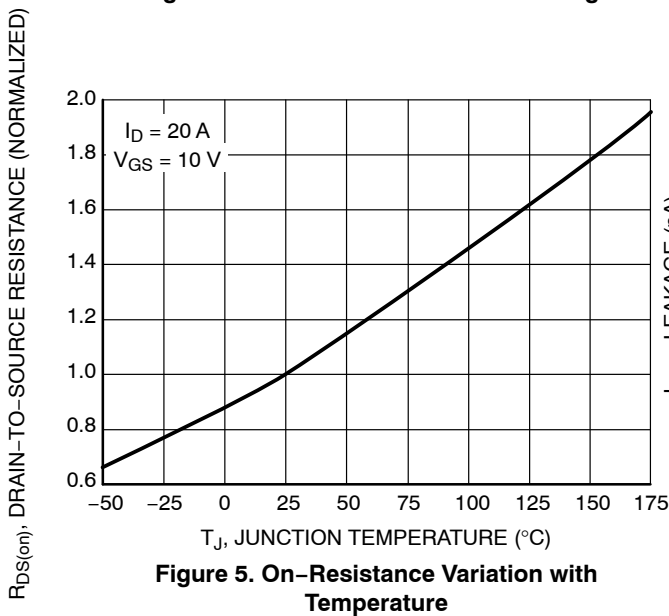


Figure 5. On-Resistance Variation with Temperature

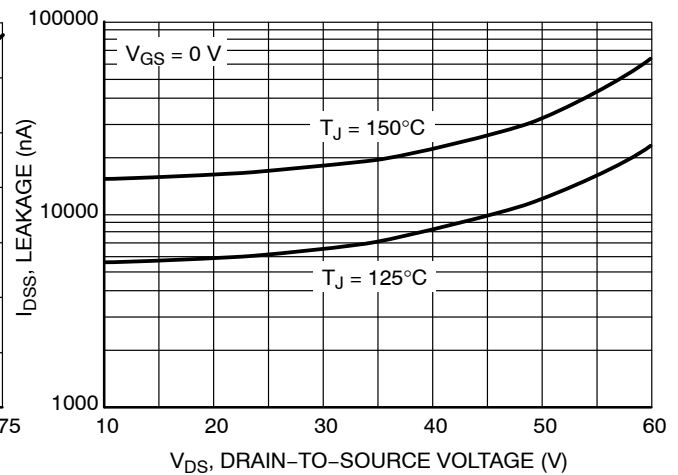


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

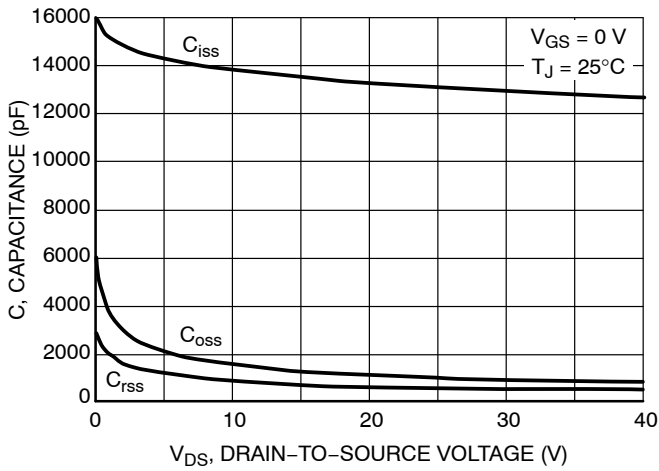


Figure 7. Capacitance Variation

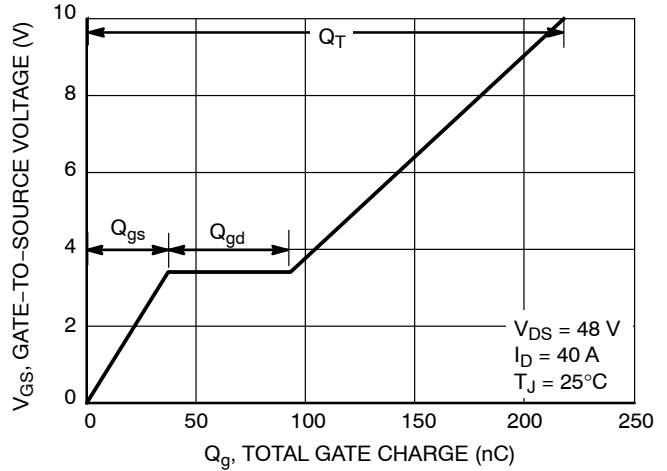


Figure 8. Gate-to-Source vs. Total Charge

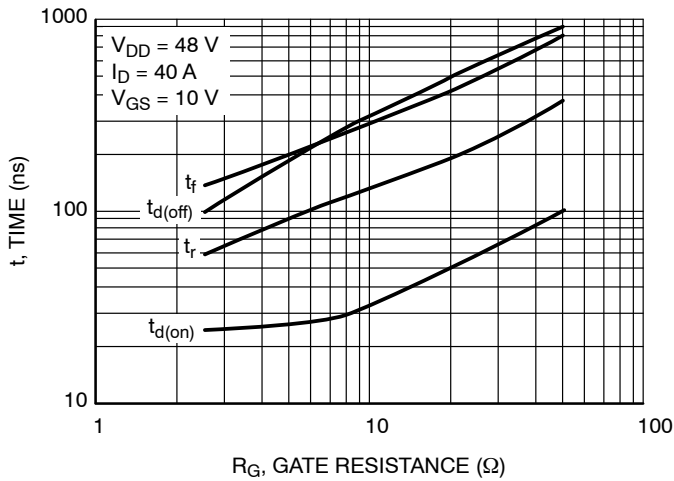


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

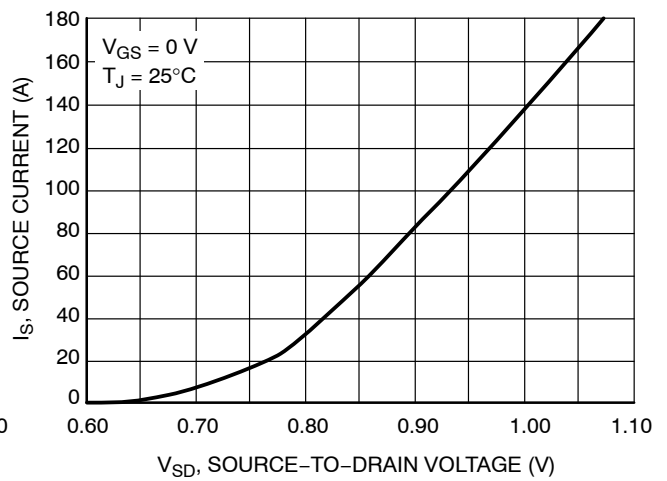


Figure 10. Diode Forward Voltage vs. Current

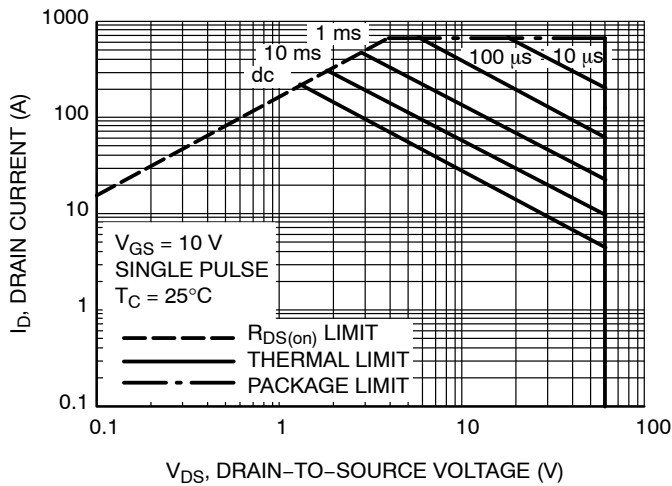


Figure 11. Maximum Rated Forward Biased Safe Operating Area

# NTB5860NL, NTP5860NL, NVB5860NL

## TYPICAL CHARACTERISTICS

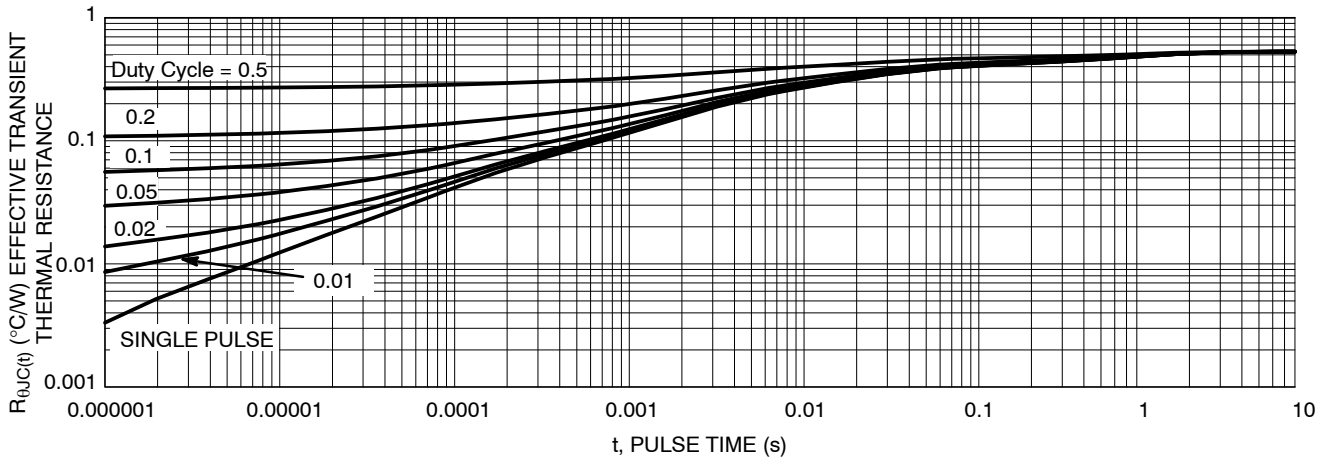


Figure 12. Thermal Response

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NTP5860NLG	TO-220AB (Pb-Free)	50 Units / Rail
NTB5860NLT4G	D <sup>2</sup> PAK (Pb-Free)	800 / Tape & Reel
NVB5860NLT4G*	D <sup>2</sup> PAK (Pb-Free)	800 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



**D<sup>2</sup>PAK 3**  
CASE 418B-04  
ISSUE L

DATE 17 FEB 2015

SCALE 1:1

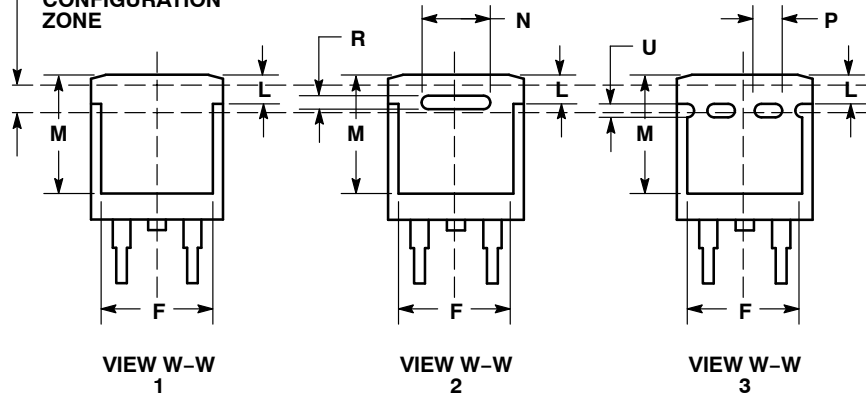


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100	BSC	2.54	BSC
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197	REF	5.00	REF
P	0.079	REF	2.00	REF
R	0.039	REF	0.99	REF
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

**VARIABLE CONFIGURATION ZONE**



- |  |   |   |  |   |  |
|--|---|---|--|---|--|
| <b>STYLE 1:</b><br>PIN 1. BASE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR | <b>STYLE 2:</b><br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE<br>4. DRAIN | <b>STYLE 3:</b><br>PIN 1. ANODE<br>2. CATHODE<br>3. ANODE<br>4. CATHODE | <b>STYLE 4:</b><br>PIN 1. GATE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR | <b>STYLE 5:</b><br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE<br>4. ANODE | <b>STYLE 6:</b><br>PIN 1. NO CONNECT<br>2. CATHODE<br>3. ANODE<br>4. CATHODE |
|--|---|---|--|---|--|

**MARKING INFORMATION AND FOOTPRINT ON PAGE 2**

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**D<sup>2</sup>PAK 3**  
CASE 418B-04  
ISSUE L

DATE 17 FEB 2015

**GENERIC  
MARKING DIAGRAM\***



- xx = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package
- AKA = Polarity Indicator

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

**SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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